

International
IR Rectifier

IR30DDR..L SERIES

HIGH POWER RECTIFIER DIODES

- **Junction Size:** **30 mm Diameter**
- **V_{RRM} Class:** **400 to 1600 V**
- **Passivation Process:** **Diffused Junction**

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	1.28V	T _J = 25°C, I _F = 1000 A
V _{RRM} Reverse Breakdown Voltage Range	400 to 1600V	T _J = 150°C, I _{RRM} = 20 mA

Mechanical Characteristics

Nominal Back Metal Composition	Al - Ni - Au
Nominal Front Metal Composition	Nickel plate Molybdenum disc
Chip Dimensions	30 mm diameter (see drawing)
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR30DDR..L Series

Bulletin I0307J 11/01

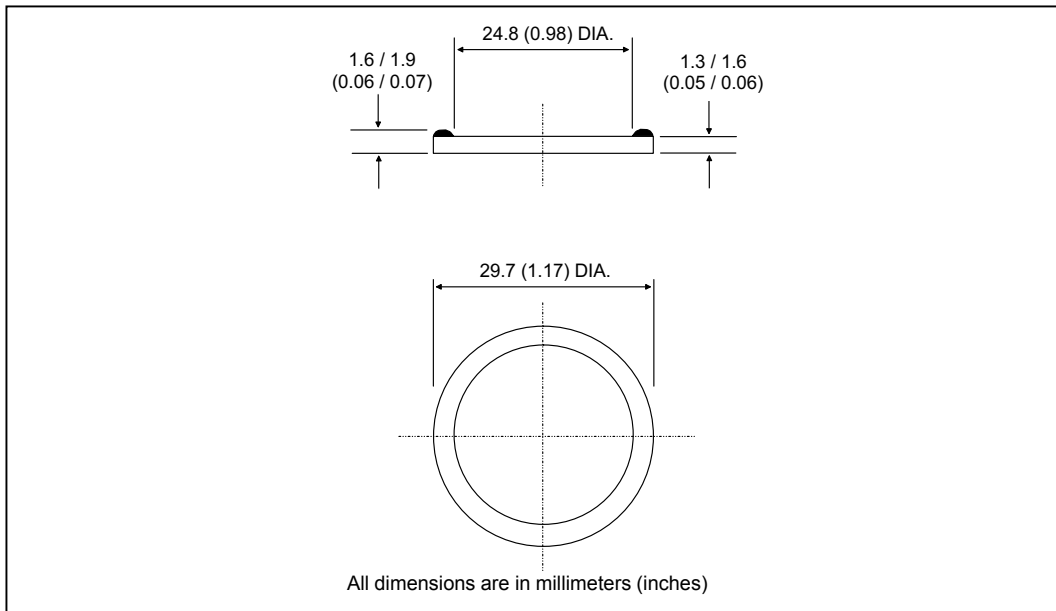
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Ordering Information Table

Device Code						
IR	30	D	D	R	16	L
①	②	③	④	⑤	⑥	⑦

<ul style="list-style-type: none"> 1 - International Rectifier device 2 - Chip Dimension in Millimeters 3 - Device identifier between chip with same diameter 4 - Type of Device: D = Standard Recovery Diode 5 - Passivation: R = Rubber for all junctions 6 - Voltage code: Code x 100 = V_{RRM} 7 - Metallization: L = Nickel plate Molybdenum disc (Anode) Al - Ni - Au (Cathode) 	<p>Available Class</p> <p>04 = 400 V</p> <p>08 = 800 V</p> <p>10 = 1000 V</p> <p>12 = 1200 V</p> <p>16 = 1600 V</p>
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Outline Table



Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

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